

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP631, TLP632

PROGRAMMABLE CONTROLLERS

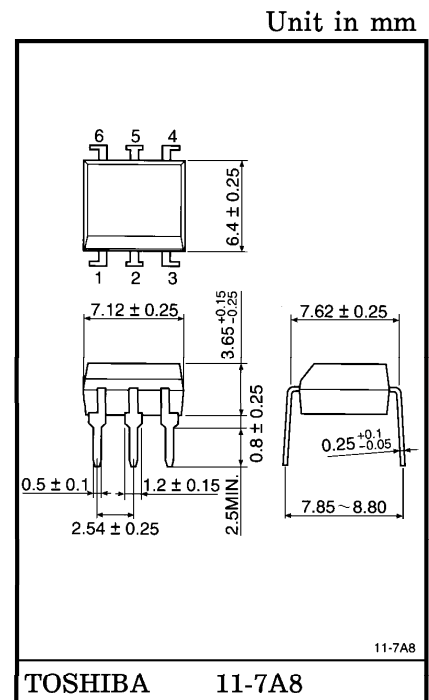
AC/DC-INPUT MODULE

SOLID STATE RELAY

The TOSHIBA TLP631 and TLP632 consist of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP.

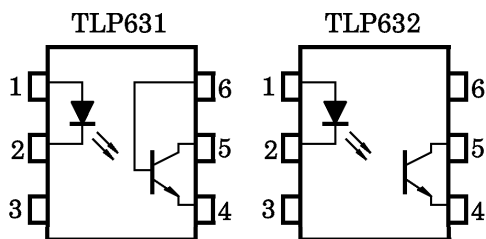
TLP632 is no-base internal connection for high-EMI environments.

- Collector-Emitter Voltage : 55V (MIN.)
- Current Transfer Ratio : 50% (MIN.)
Rank GB : 100% (MIN.)
- Isolation Voltage : 5000V_{rms} (MIN.)
- UL Recognized : UL1577, File No. E67349



Weight : 0.4g

PIN CONFIGURATIONS (TOP VIEW)



- | | |
|---------------|---------------|
| 1 : ANODE | 1 : ANODE |
| 2 : CATHODE | 2 : CATHODE |
| 3 : N.C. | 3 : N.C. |
| 4 : EMITTER | 4 : EMITTER |
| 5 : COLLECTOR | 5 : COLLECTOR |
| 6 : BASE | 6 : N.C. |

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current	I _F	60	mA
	Forward Current Derating (Ta ≥ 39°C)	ΔI _F / °C	−0.7	mA / °C
	Peak Forward Current (100 μs pulse, 100pps)	I _{FP}	1	A
	Reverse Voltage	V _R	5	V
	Junction Temperature	T _j	125	°C
DETECTOR	Collector-Emitter Voltage	V _{CEO}	55	V
	Collector-Base Voltage (TLP631)	V _{CBO}	80	V
	Emitter-Collector Voltage	V _{ECO}	7	V
	Emitter-Base Voltage (TLP631)	V _{EBO}	7	V
	Collector Current	I _C	50	mA
	Power Dissipation	P _C	150	mW
	Power Dissipation Derating (Ta ≥ 25°C)	ΔP _C / °C	−1.5	mW / °C
	Junction Temperature	T _j	125	°C
Storage Temperature Range		T _{stg}	−55~125	°C
Operating Temperature Range		T _{opr}	−55~100	°C
Lead Soldering Temperature (10s)		T _{sol}	260	°C
Total Package Power Dissipation		P _T	250	mW
Total Package Power Dissipation Derating (Ta ≥ 25°C)		ΔP _T / °C	−2.5	mW / °C
Isolation Voltage (AC, 1 min., R.H. ≤ 60%)		BV _S	5000	V _{rms}

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V _{CC}	—	5	24	V
Forward Current	I _F	—	16	25	mA
Collector Current	I _C	—	1	10	mA
Operating Temperature	T _{opr}	−25	—	85	°C

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	30	—	pF
DETECTOR	Collector-Emitter Breakdown Voltage	$V_{(BR) CEO}$	$I_C = 0.5\text{mA}$	55	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR) ECO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector-Base Breakdown Voltage (TLP631)	$V_{(BR) CBO}$	$I_C = 0.1\text{mA}$	80	—	—	V
	Emitter-Base Breakdown Voltage (TLP631)	$V_{(BR) EBO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector Dark Current	I_{CEO}	$V_{CE} = 24\text{V}$	—	10	100	nA
			$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$	—	2	50	μA
	Capacitance Collector to Emitter	C_{CE}	$V = 0, f = 1\text{MHz}$	—	10	—	pF

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I_C / I_F	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F (\text{sat})$	$I_F = 1\text{mA}, V_{CE} = 0.4\text{V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-Emitter Saturation Voltage	$V_{CE (\text{sat})}$	$I_C = 2.4\text{mA}, I_F = 8\text{mA}$	—	—	0.4	V

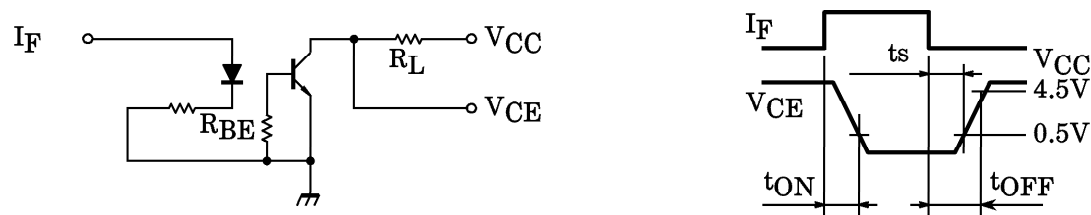
ISOLATION CHARACTERISTICS (Ta = 25°C)

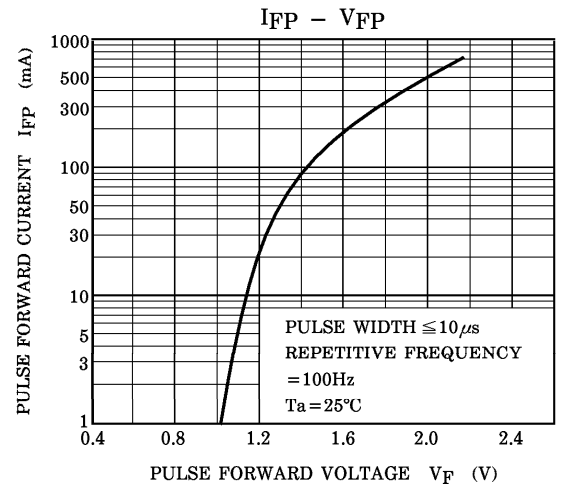
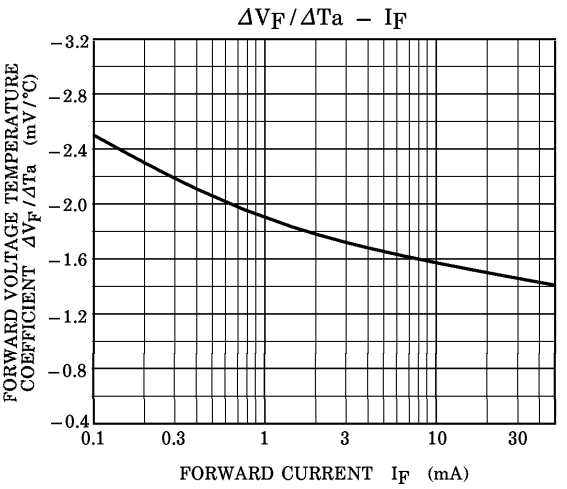
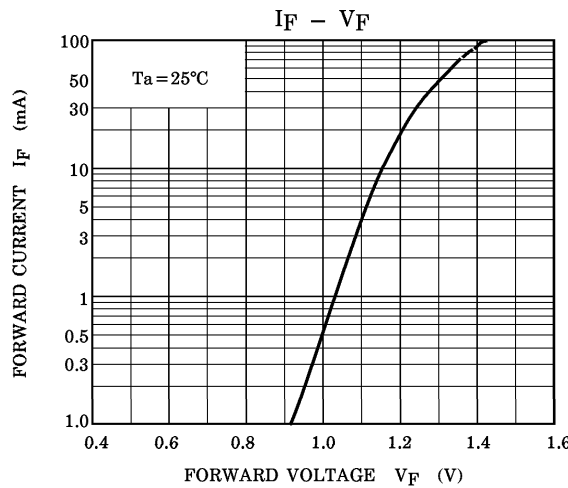
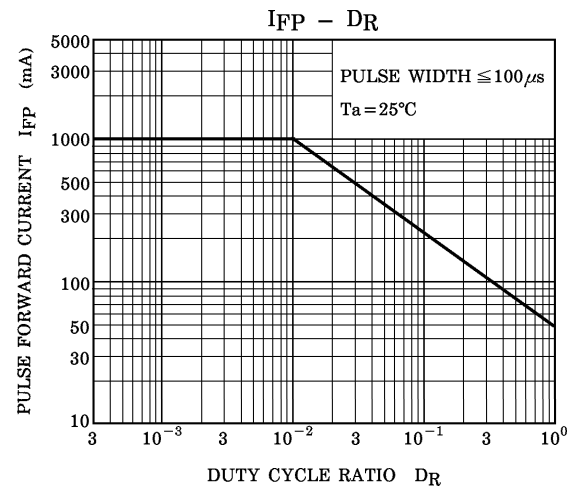
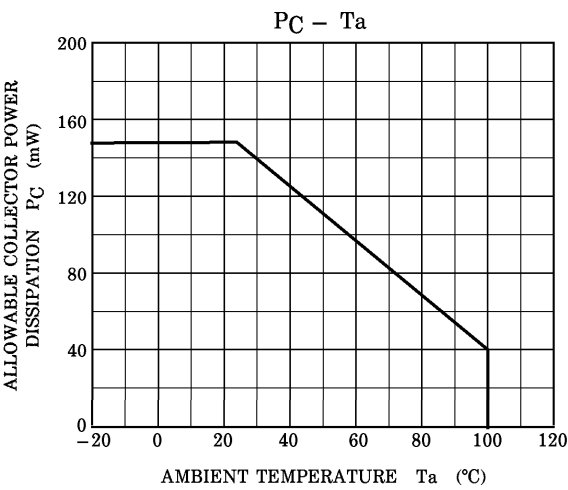
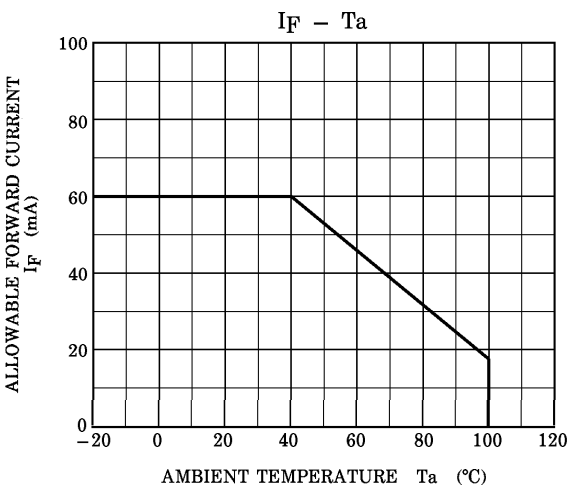
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	CS	VS=0, f=1MHz	—	0.8	—	pF
Isolation Resistance	RS	VS=500V, R.H.≤60%	5×10 ¹⁰	10 ¹⁴	—	Ω
Isolation Voltage	BVS	AC, 1 minute	5000	—	—	Vrms
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	Vdc

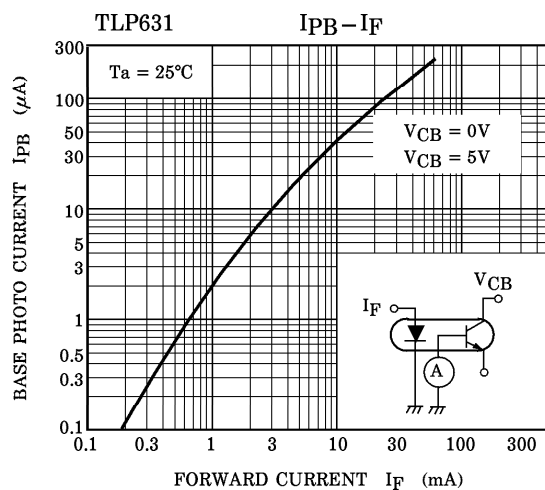
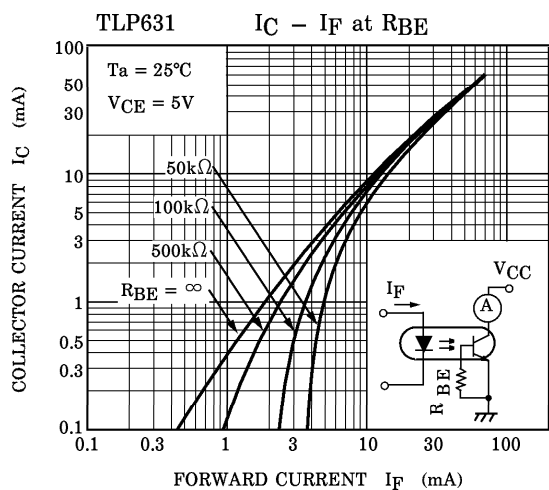
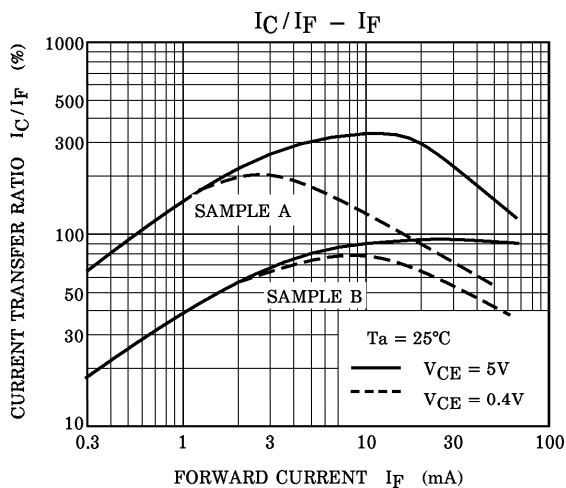
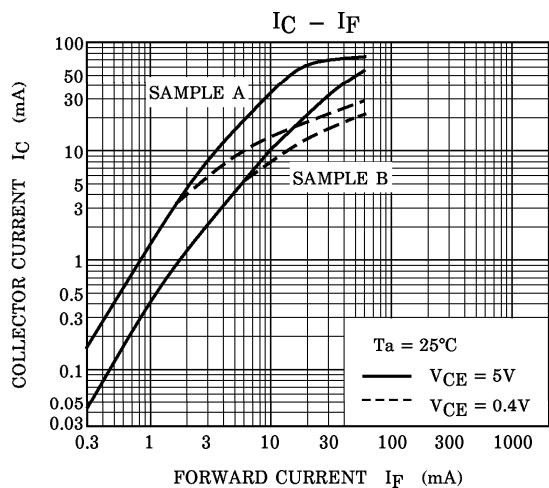
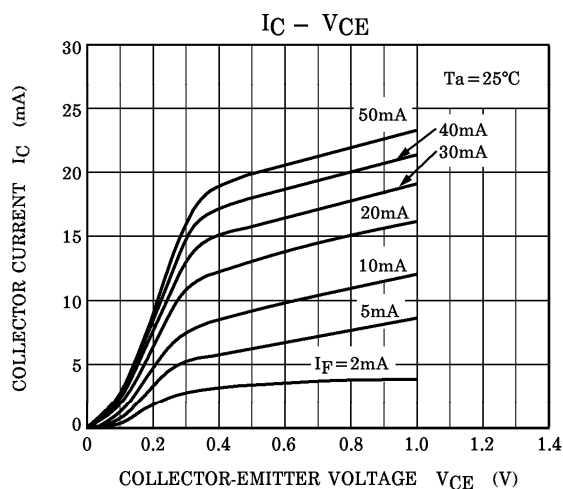
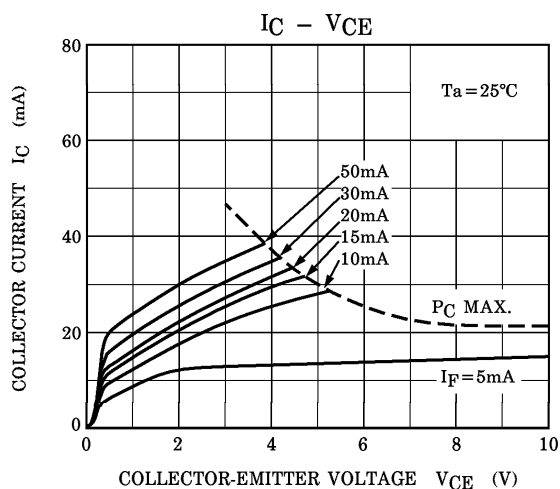
SWITCHING CHARACTERISTICS (Ta = 25°C)

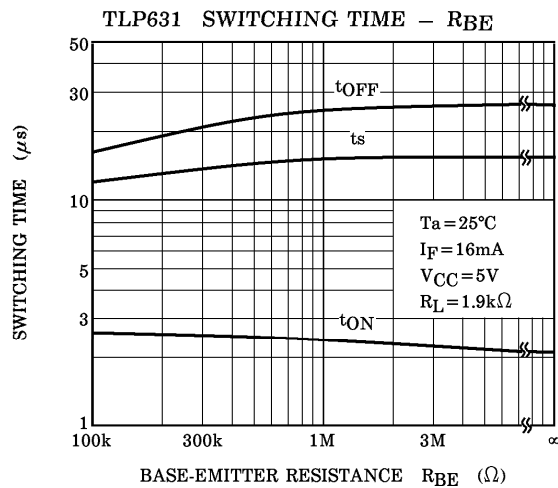
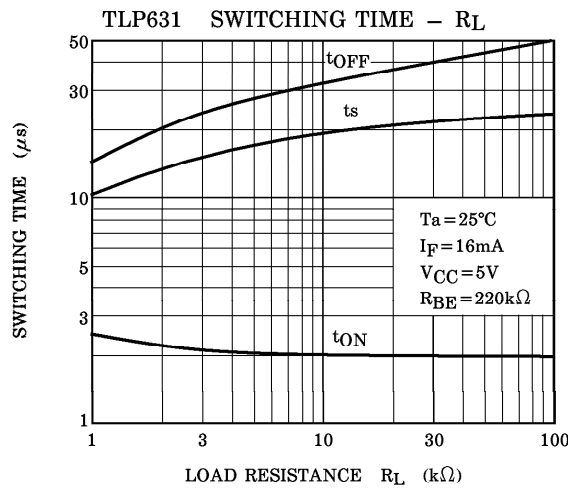
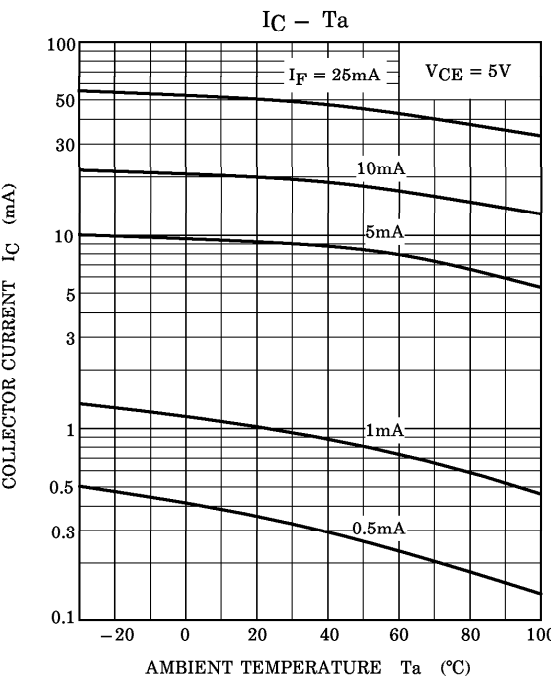
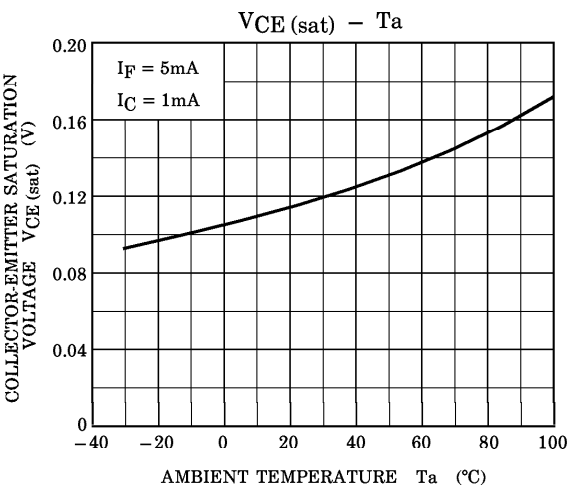
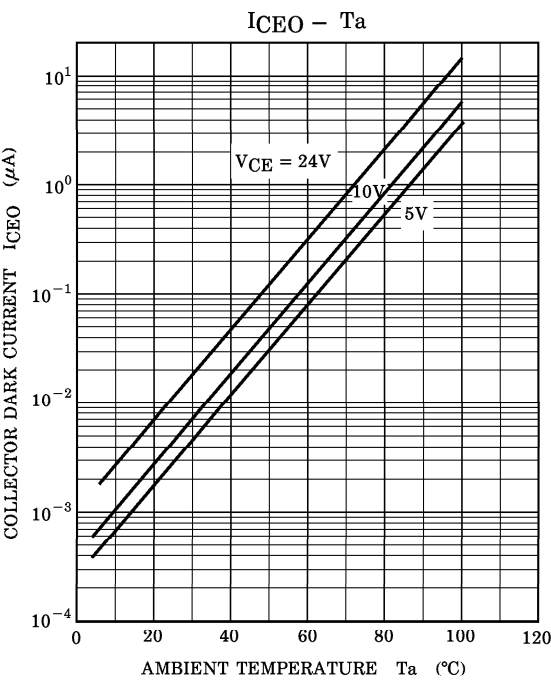
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	tr	VCC=10V, IC=2mA RL=100Ω	—	2	—	μs
Fall Time	tf		—	3	—	
Turn-on Time	ton		—	3	—	
Turn-off Time	toff		—	3	—	
Turn-on Time	tON	RL=1.9kΩ (Fig.1) RBE=OPEN VCC=5V, IF=16mA	—	2	—	μs
Storage Time	ts		—	15	—	
Turn-off Time	tOFF		—	25	—	
Turn-on Time	tON	RL=1.9kΩ (Fig.1) RBE=220kΩ (TLP631) VCC=5V, IF=16mA	—	2	—	μs
Storage Time	ts		—	12	—	
Turn-off Time	tOFF		—	20	—	

Fig.1 SWITCHING TIME TEST CIRCUIT









RESTRICTIONS ON PRODUCT USE

000707EBC

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